

# High Voltage IGBT

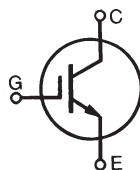
## IXGT6N170AHV

$$V_{CES} = 1700V$$

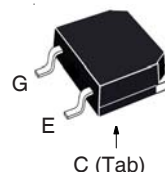
$$I_{C25} = 6A$$

$$V_{CE(sat)} \leq 7.0V$$

$$t_{fi(typ)} = 32ns$$



TO-268



G = Gate      C = Collector  
E = Emitter    Tab = Collector

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $150^\circ C$	1700	V
$V_{CGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GE} = 1M\Omega$	1700	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$	6	A
$I_{C110}$	$T_C = 110^\circ C$	3	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	14	A
<b>SSOA</b>	$V_{GE} = 15V$ , $T_{VJ} = 125^\circ C$ , $R_G = 33\Omega$	$I_{CM} = 12$	A
<b>(RBSOA)</b>	Clamped Inductive Load	$0.8 \cdot V_{CES}$	
$t_{sc}$ <b>(SCSOA)</b>	$V_{GE} = 15V$ , $V_{CE} = 1200V$ , $T_J = 125^\circ C$ $R_G = 33\Omega$ , Non Repetitive	10	$\mu s$
$P_C$	$T_C = 25^\circ C$	75	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
$T_{SOLD}$	Plastic Body for 10 seconds	260	$^\circ C$
<b>Weight</b>		4	g

### Features

- High Blocking Voltage
- High Voltage Package

### Advantages

- High Power Density
- Easy to Mount

### Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Welding Machines

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu A$ , $V_{GE} = 0V$	1700		V
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.0		5.0 V
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$ , $V_{GE} = 0V$ $T_J = 125^\circ C$			10 $\mu A$ 500 $\mu A$
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 3A$ , $V_{GE} = 15V$ , Note 1 $T_J = 125^\circ C$		5.4	7.0 V V

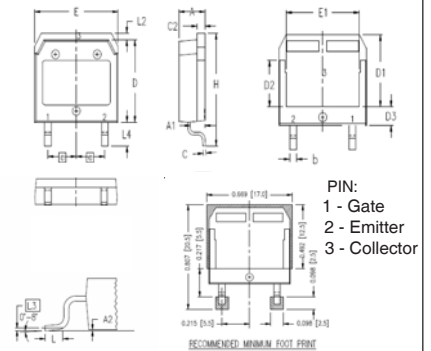
### Symbol Test Conditions

( $T_J = 25^\circ\text{C}$  Unless Otherwise Specified)

### Characteristic Values

		Min.	Typ.	Max.	
$g_{fs}$	$I_C = 6\text{A}, V_{CE} = 20\text{V}, \text{Note 1}$	2.0	3.5		S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		390		pF
$C_{oes}$			20		pF
$C_{res}$			7		pF
$Q_{g(on)}$	$I_C = 6\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		18.5		nC
$Q_{ge}$			2.8		nC
$Q_{gc}$			8.2		nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 6\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 33\Omega$ Note 2		46		ns
$t_{ri}$			40		ns
$E_{on}$			0.59		mJ
$t_{d(off)}$			220	400	ns
$t_{fi}$			32		ns
$E_{off}$			0.18	0.36	mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = 6\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 33\Omega$ Note 2		48		ns
$t_{ri}$			43		ns
$E_{on}$			0.62		mJ
$t_{d(off)}$			230		ns
$t_{fi}$			41		ns
$E_{off}$			0.25		mJ
$R_{thJC}$				1.65	$^\circ\text{C/W}$

### TO-268 (VHV) Outline



SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.465	.476	11.80	12.10
D2	.295	.307	7.50	7.80
D3	.114	.126	2.90	3.20
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
E	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.067	.079	1.70	2.00
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

### Notes:

1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Switching times & energy losses may increase for higher  $V_{CE}(\text{clamp})$ ,  $T_J$  or  $R_G$ .

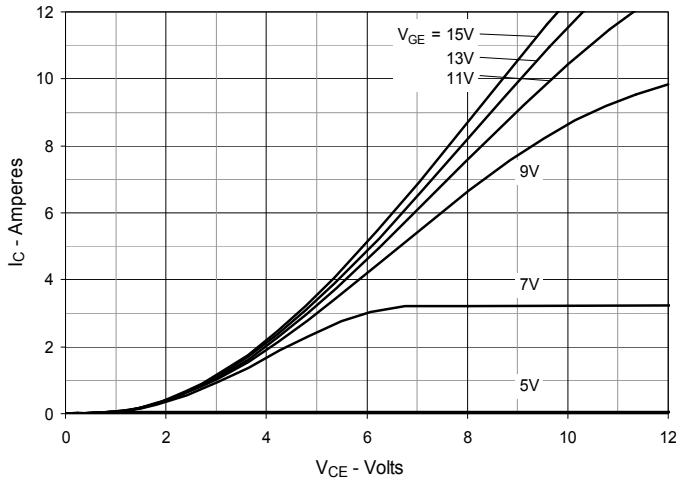
### ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

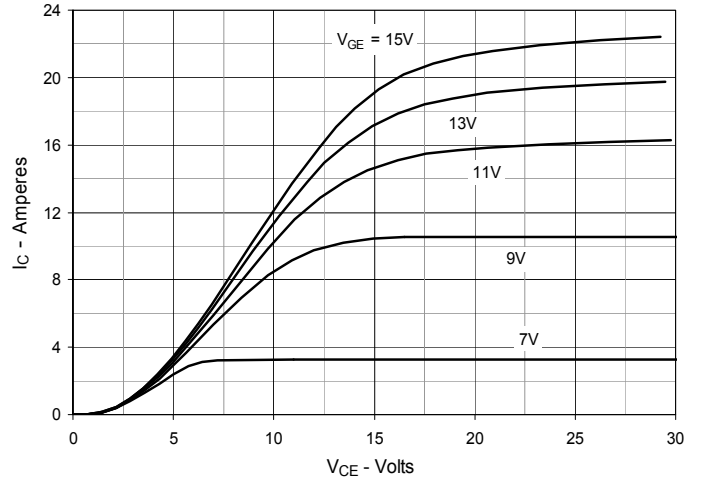
### IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

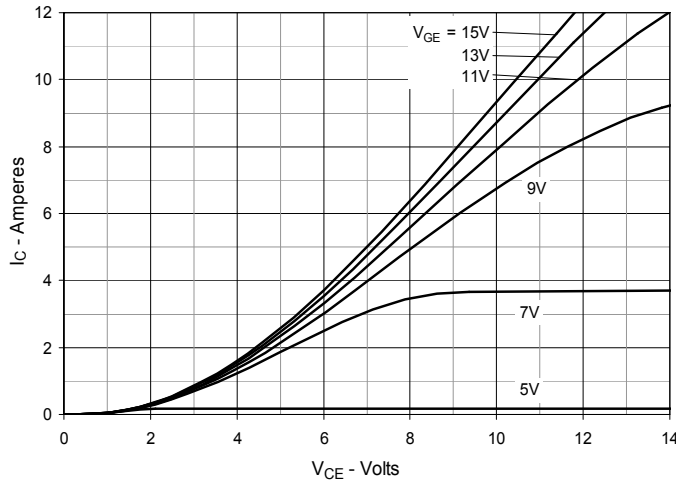
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



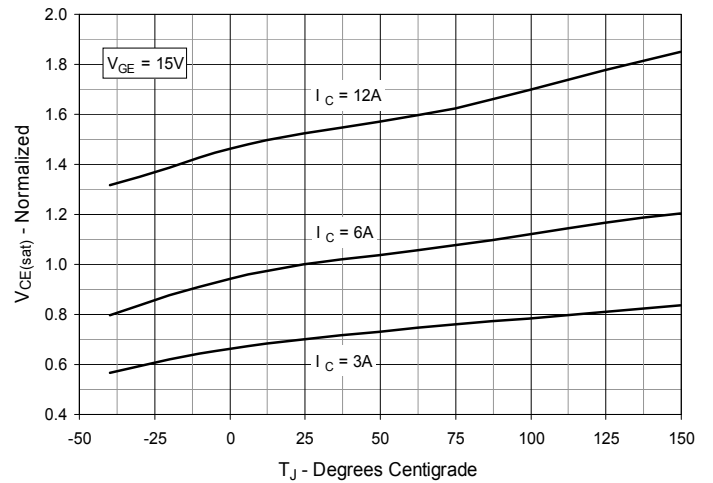
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



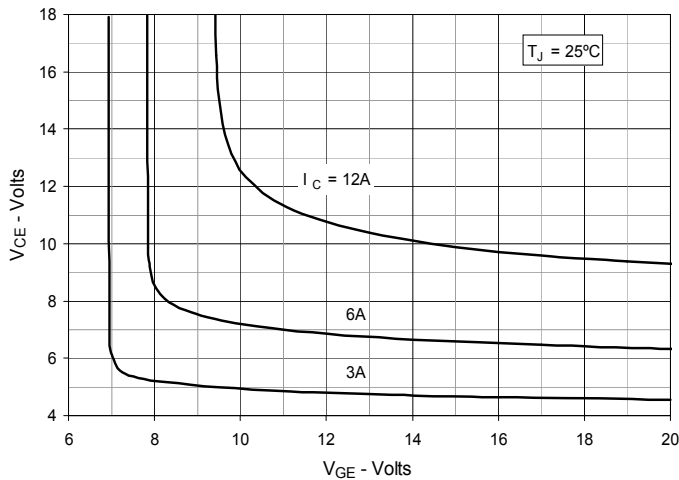
**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$**



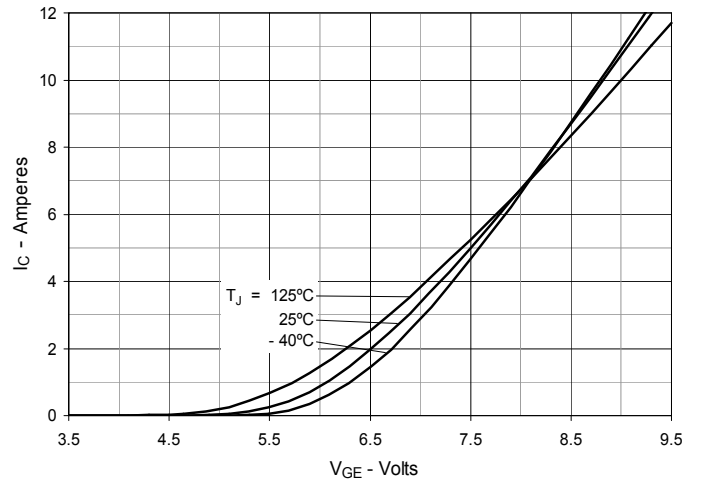
**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**



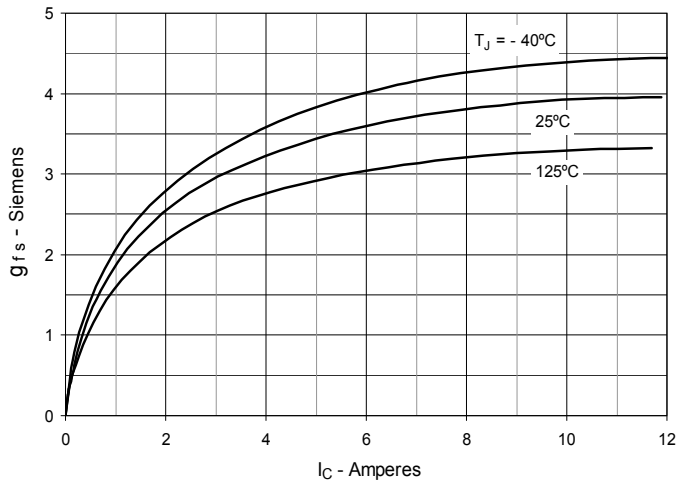
**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**



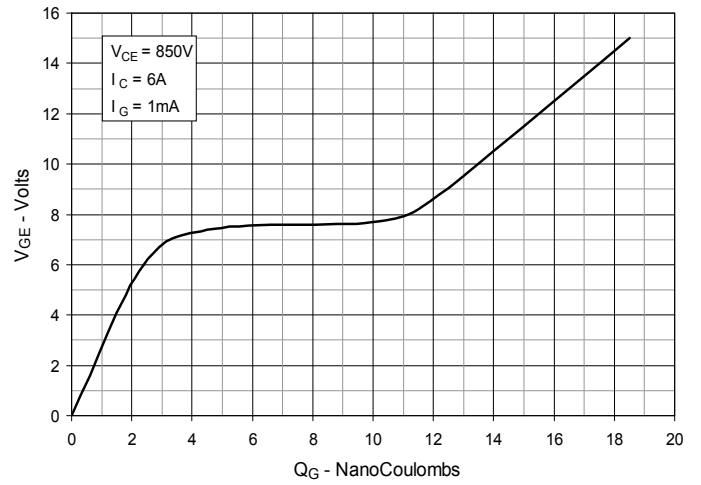
**Fig. 6. Input Admittance**



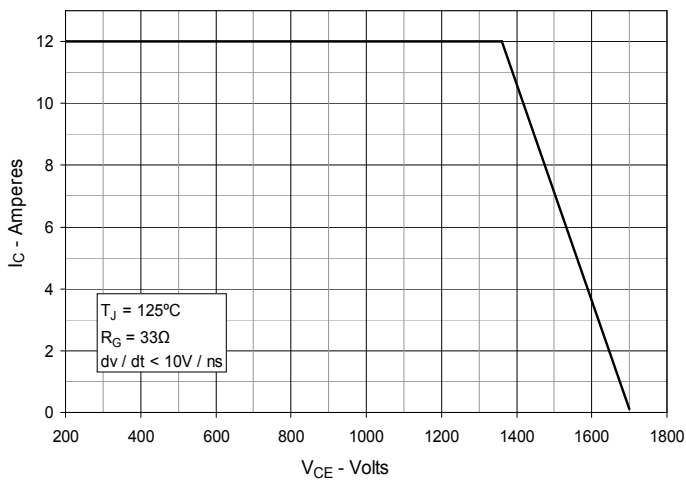
**Fig. 7. Transconductance**



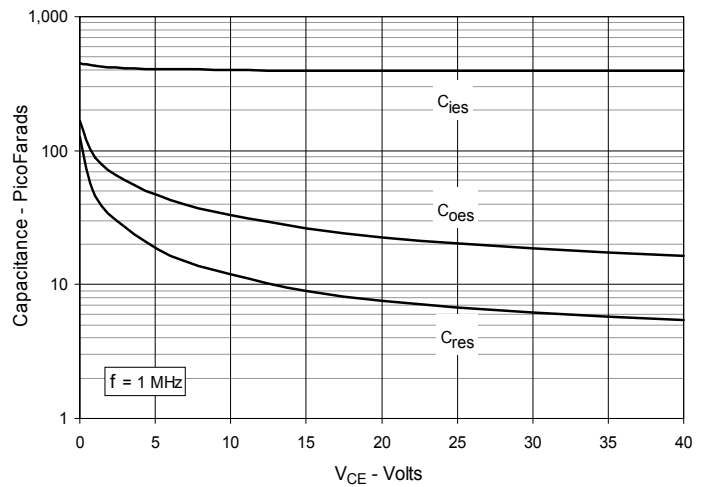
**Fig. 8. Gate Charge**



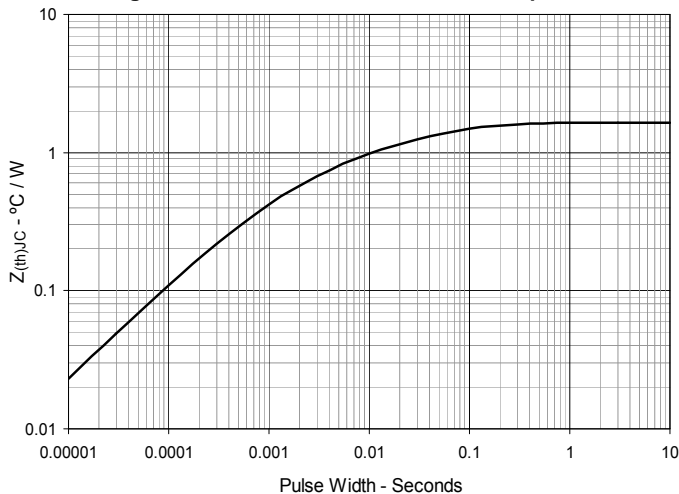
**Fig. 9. Reverse-Bias Safe Operating Area**



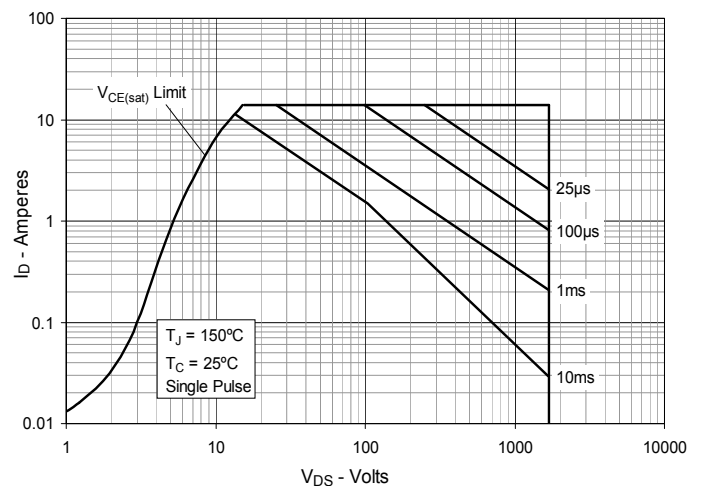
**Fig. 10. Capacitance**



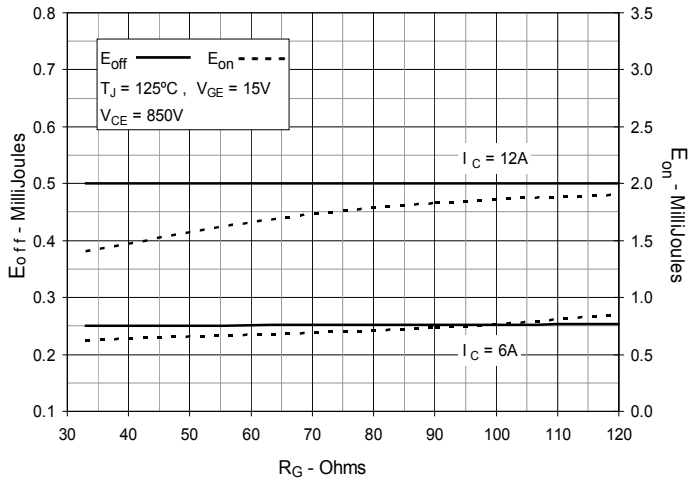
**Fig. 11. Maximum Transient Thermal Impedance**



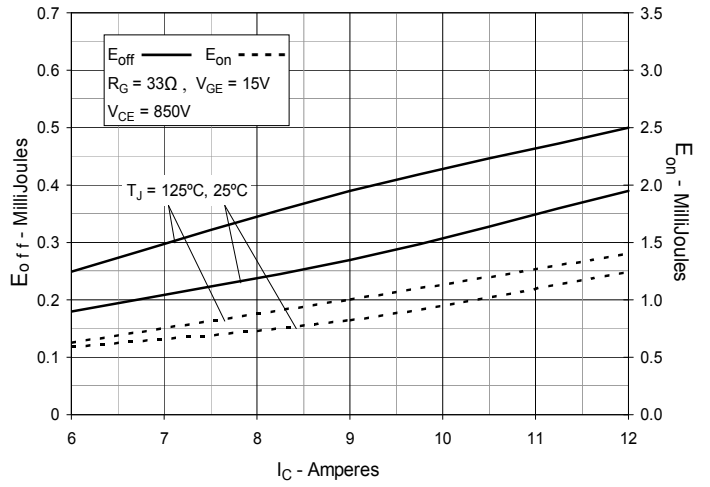
**Fig. 12. Forward-Bias Safe Operating Area**



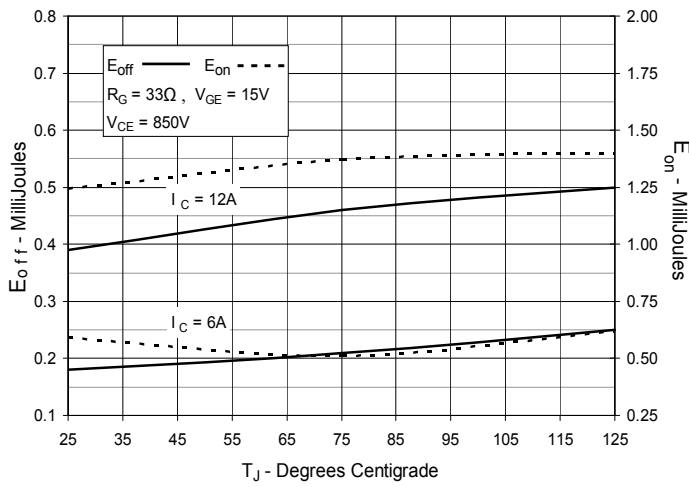
**Fig. 13. Inductive Switching Energy Loss vs. Gate Resistance**



**Fig. 14. Inductive Switching Energy Loss vs. Collector Current**



**Fig. 15. Inductive Switching Energy Loss vs. Junction Temperature**





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